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## **Femtosecond and nanosecond pulsed laser deposition of silicon and germanium**

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### **Submission of a paper to Applied Surface Science**

### **Femtosecond and nanosecond pulsed laser deposition of Si and Ge**

#### **Highlights**

- Ge and Si were deposited by fs and ns laser at room temperature and at vacuum.
- Ion of  $10^4 \text{ ms}^{-1}$  and 30-200 eV was obtained for ns ablation for Ge and Si.
- Highly energetic ions of  $10^5 \text{ ms}^{-1}$  with 2-7 KeV were produced in fs laser ablation.
- Nanocrystalline Si and Ge were deposited by using fs laser.
- Nanoparticles  $< 10 \text{ nm}$  haven been obtained by fs laser.

#### **Abstract**

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